## HiperLCS-2 Chipset



## Off-Line LLC Switcher ICs with Integrated 600 V FREDFETs Synchronous Rectification and FluxLink Feedback

## **Product Highlights**

#### **Highly Integrated, Compact Footprint**

- Up to 98.1% efficiency
- Very low component count and small footprint package
- Eliminates heat sink up to 220 W continuous
- Self-powered start-up
- 600 V FREDFET, rugged fast recovery body diode, current sensing
- HB auto dead time and hard switch detect
- Selectable center frequency (90, 120, 180, 240 kHz)
- Secondary-side sensing and feedback control with fast transient response
- Synchronous rectification driver
- Integrated FluxLink<sup>™</sup>, HIPOT-isolated control link

#### EcoSmart<sup>™</sup> – Energy Efficient

- As low as 41 mW no-load including line sense
- Output always in regulation, 0-100% load step
- · Easily meets all global energy efficiency regulations

#### Advanced Protection / Safety Features

- HB and SR shoot-through protection
- Power-up pin open/short check
- System short-circuit, thermal, HB OCP, FB open, fast input line UV/OV and PMAX protection

#### **Optional Features**

- · Auto-restart or latching fault response for output OVP/UVP
- Latching or hysteretic primary over-temperature protection
- External fault detect and remote on/off
- Inrush-relay drive output pin
- Provides start-up bias for PFC stage

#### **Full Safety and Regulatory Compliance**

- Reinforced isolation, isolation voltage >4000 VAC
- UL1577, CQC and TUV (EN62368-1) safety approved

## Applications

- High efficiency power supplies up to 220 W continuous
- Consumer electronics TV, PC, e-bike and tool chargers

### Description

The HiperLCS<sup>™</sup>-2 chipset achieves high efficiency and compact size for up to 220 W with no heat sink. This IC chipset simplifies the design and manufacture of LLC resonant power converters. The LCS72xxC primary-side devices incorporate 600 V FREDFET in a half-bridge arrangement with control, level shifting, drive and self-powered start-up. The LSR2000C master controller device provides reinforced isolated feedback, output sensing and SR management.

HiperLCS-2 chipset incorporate multiple protection features including: line over and undervoltage protection, output overvoltage and over-temperature shutdown. Device fault response options support common combinations of latching and auto-restart behaviors required by applications such as chargers, adapters, consumer electronics and industrial systems.

## **Output Power Table**

Power Device	Safety Isolation	385 VDC ±5%			
	Device	<b>Adapter</b> <sup>1</sup>	Peak Power <sup>2</sup>		
LCS7260C	LSR2000C	80 W	135 W		
LCS7262C		120 W	205 W		
LCS7265C		220 W	375 W		

Table 1. Output Power Table.

Notes:

- Power Device: Minimum continuous power in a typical non-ventilated enclosed typical size adapter measured at 40 °C ambient. Max output power is dependent on the design, with condition that T, <110 °C.</li>
- 2. Power Device: Minimum peak power capability (not thermally limited).

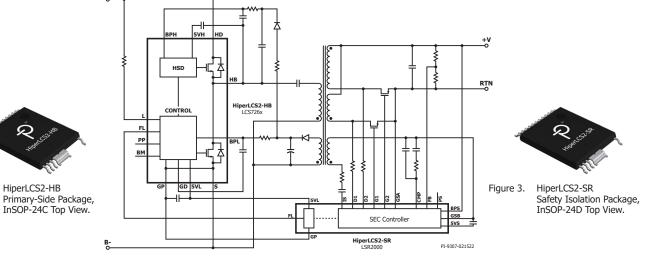


Figure 1. Typical Application Schematic.

Figure 2.

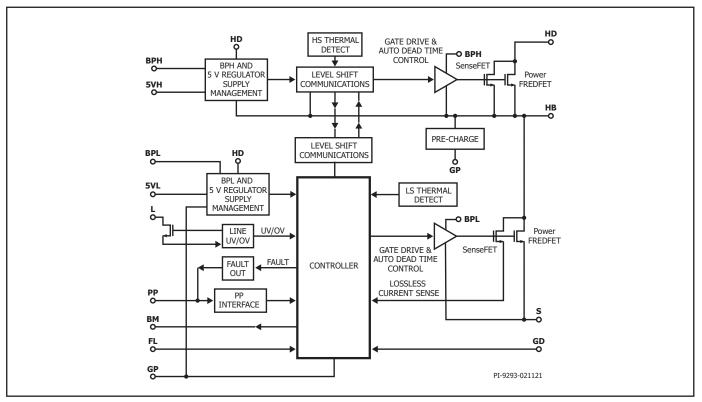


Figure 4. Primary Controller (Low-Side and High-Side), Block Diagram.

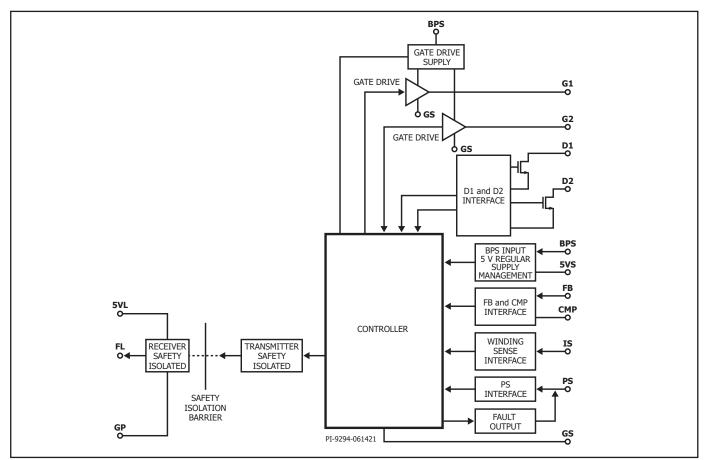


Figure 5. Safety Isolation and Secondary Controller Block Diagram.



# Pin Functional Description – Primary-Side Device LCS726xC

#### Low-Side

#### PRIMARY GROUND (GD) (Pin 1)

Primary gate-drive ground. Should be capacitively decoupled to primary supply pin (BPL).

#### BURST MODE (BM) (Pin 2)

Small signal output indicating deep burst mode operation. Can be coupled to control external primary-side circuits.

#### PRIMARY GROUND (GP) (Pin 3)

Small signal primary ground. Should be capacitively decoupled to primary 5 V (5VL) pin.

#### NO CONNECTION (NC) (Pin 4)

Pin not connected. Leave open.

#### BYPASS LOW-SIDE (BPL) (Pin 5)

Power supply pin for primary low-side device. Should be capacitively decoupled to primary gate-drive ground (GD) pin.

## PRIMARY LOW-SIDE 5 V (5VL) (Pin 6)

Primary low-side small signal 5 V IC-supply pin. Also provides bias power to the Primary-side of the Isolation device (LSR2000). 5VL should be capacitively decoupled to primary small signal ground (GP).

#### FLUXLINK INPUT (FL) (Pin 7)

Small signal input for FLUX LINK signal.

#### PROGRAM PRIMARY (PP) (Pin 8)

Small signal connection for customer configuration selection components. Also used in some configurations as small signal current input to receive power-good (remote on/off), signal to command device activation. Likewise used in some configurations as small signal current input for external fault. This pin also outputs logic level error code during fault conditions.

#### NO CONNECT (NC) (Pin 9)

Pin not connected. Leave open.

PRIMARY GROUND (GP) (Pin 10)

Small signal primary ground. Should be capacitively decoupled to primary 5 V (5VL) pin.

#### NO CONNECT (NC) (Pin 11)

Pin not connected. Leave open.

#### LINE SENSE (L) (Pin 12)

High-voltage small signal current input pin. Used to detect line-input voltage. Also used in some configurations as small signal input to receive power-good (remote on/off) signal to command device activation

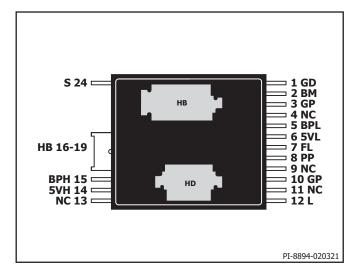


Figure 6. HiperLCS-2 Primary-Side LCS726xC, InSOP-24C (Bottom View).

#### **High-Side**

#### NO CONNECT (NC) (Pin 13)

Pin not connected. Leave open.

#### HIGH-SIDE 5 V (5VH) (Pin 14)

Primary high-side small signal 5 V IC-supply pin. Should be capacitively decoupled to half-bridge (HB). NOTE: this pin floats on the half-bridge switching voltage, can be at high-voltage with respect to primary grounds.

#### BYPASS HIGH-SIDE (BPH) (Pin 15)

Power supply for primary high-side device. Should be capacitively decoupled to half-bridge (HB) pin. NOTE: this pin floats on the half-bridge switching voltage, can be at high-voltage with respect to primary grounds.

#### HALF-BRIDGE (HB) (Pins 16-19 and Back Side HB Pad)

High-voltage and high current connection point for low-side MOSFET DRAIN and high-side MOSFET SOURCE. The half-bridge node typically switches between primary ground and primary input bus (HD).

#### SOURCE (S) (Pin 24)

High current Power ground return for half-bridge switch current. Also at same potential as other small-signal primary grounds.

#### HD (Pin Back-Side Solder Pad)

High current, high-side MOSFET Drain and connection to system high-voltage input bus.



HiperLCS2–HB, Primary-Side Packages. InSOP-24C Top View, InSOP-24C Bottom View.

## Pin Functional Description – Safety Isolation and Secondary-Side Device LSR2000C

#### SECONDARY 5 V (5VS) (Pin 1)

Connection point for an external decoupling capacitor for the secondary IC supply. Should be capacitively decoupled to secondary ground (GSB).

#### SECONDARY GROUND (GSB) (Pin 2)

Ground for the secondary IC.

#### WINDING SENSE (IS) (Pin 3)

Secondary-side, small signal current input connection to an external resistor and capacitor.

#### COMPENSATION (CMP) (Pin 4)

Secondary-side, small signal connection to external frequency compensation resistor capacitor network.

#### FEEDBACK (FB) (Pin 5)

Secondary-side, small signal feedback signal to secondary control.

#### PROGRAM SECONDARY (PS) (Pin 6)

Secondary-side, small signal connection for customer configuration selection components. This pin also outputs logic level fault code during fault conditions.

#### SECONDARY BYPASS (BPS) (Pin 7)

Secondary-side power supply pin for secondary device.

#### SR GATE2 DRIVE (G2) (Pin 8)

Secondary-side, output for driving secondary synchronous rectifier (SR) MOSFET for first output phase.

#### SR GATE1 DRIVE (G1) (Pin 9)

Secondray-side, output for driving secondary synchronous rectifier (SR) MOSFET for second output phase.

#### SR DRAIN2 SENSE (D2) (Pin 10)

Secondary-side, medium voltage small signal input for sensing SR DRAIN/SOURCE voltage.

#### SR DRAIN1 SENSE (D1) (Pin 11)

Secondary-side, medium voltage small signal input for sensing SR DRAIN/SOURCE voltage.

#### SECONDARY GROUND (GSA) (Pin 12)

Internally connected to secondary ground (GSB).

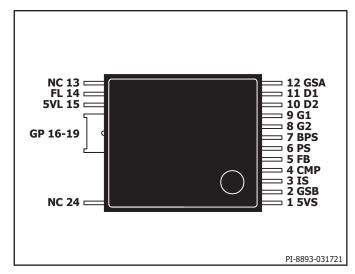


Figure 7. HiperLCS-2 Safety Isolation and Secondary-Side LSR2000C, InSOP-24D (Top View).

#### NO CONNECT (NC) (Pin 13)

No connection. Leave open.

#### FLUXLINK (FL) (Pin 14)

Primary-side small signal output is the FLUXLINK primary output pin.

## PRIMARY 5V (5VL) (Pin 15)

Primary-side connection point for an external primary decoupling capacitor for the primary IC supply. Should be capacitively decoupled to primary ground (GP)

## PRIMARY GROUND (GP) (Pins 16-19)

Primary-side ground reference for primary BYPASS pin.

#### NO CONNECT (NC) (Pin 24) No connection. Leave open.



HiperLCS2–SR, Safety Isolation Package. InSOP-24D Top View, InSOP-24D Bottom View.



## **HiperLCS-2 Basic Operation**

The HiperLCS-2 is designed for half-bridge LLC converters, which are high-efficiency resonant ZVS, variable frequency converters.

HiperLCS-2 comes as a chipset with two devices: the power-device, and the isolation device. The power-device (LCS726x), is on the primary side of the isolation barrier and includes an LLC controller with built-in high-side and low-drivers and half-bridge power-MOSFETs. The isolation-device (LSR2000), straddles the isolation barrier to facilitate communications to the power-device (primary device). The isolation-device also includes the secondary controller and SR-driver. The HiperLCS-2 is able to operate with nominal frequencies of up to 240 kHz. It offers extremely high conversion efficiency coupled with low-component count and rugged protection features.

#### **HiperLCS-2 Primary-Side Power-Device Operation**

#### Start-Up Self-Bias

The HiperLCS-2 provides self-powered start-up. This means that the system provides a high-voltage bus to the HD pin and the HiperLCS-2 device will take care the rest. Self powering is accomplished using internal high-voltage current sources. The first current source is connected between HD and the BPL pin. When voltage is applied to HD, the BPL will begin to charge any capacitance connected to this pin. There is a low pre-charge current which allows initial charging voltage to be established, and then as BPL voltage increases, this charge current is stepped to a much higher level allowing faster start-up times. This higher current capability of the BPL charging also allows the HiperLCS-2 to provide bias power to a PFC stage and allow the PFC to begin switching prior to the HiperLCS-2. Once the BPL self-charge reaches the target voltage it will enter hysteretic control. The internal current source is disabled during normal operation once an external bias (from a transformer bias winding), becomes active. The BPH pin is charged in very similar way to BPL, but the charge current from HD to BPH is lower. The BPH pin internal charge current will likewise be disabled once external bias becomes available.

In order to begin switching of an LLC converter ideally we would prefer the half-bridge and resonant capacitor voltages to be in a known condition (preferably close to zero). The HiperLCS-2 achieves this using a high-voltage current source connected to the HB pin. This HB current source pre-conditions the resonant tank components pulling current to ground (return), prior to beginning switching. Doing this means that at initial start or restart, the HiperLCS-2 will always start with known tank conditions. The result is that the HiperLCS-2 can achieve resonant switching on the second switch edge. The pre-condition HB-current source is active prior to switching while the high-side device is below UV condition.

After all the charging conditions are complete and all undervoltage conditions are cleared, HiperLCS-2 begins switching with the high-side power-MOSFET first.

#### Start-Up Primary Soft-Start

The HiperLCS-2 begins primary switching at a frequency approximately 1.5x the maximum of the selected switching frequency range. The switching frequency is ramped down quickly to build current in the resonant tank. Once the resonant tank achieves target current ( $I_{ovt}$ ), the frequency is then indirectly regulated to maintain tank current at this level. The result at the system output capacitor, is equivalent to a very high-power current source. This results in a monotonic rise at the voltage on the output capacitor. The positive slew rate of the output voltage-rise will be a function of resonant tank and output capacitor values. Engagement of arbitrary output loads will slow the output voltage-rise but will not change the polarity of the output

voltage slope. Primary control of the switching continues until the output voltage reaches close to regulation at which point the secondary will take control of the switching.

#### **Auto Dead Time**

The LLC-converter has a structure where positive and return voltages connect sequentially via power-MOSFET's to the mid-point or half-bridge node. The half-bridge connects to a resonant-tank network which is then series connected to typically power-return (ground) and coupled to output load. The high-side power-MOSFET and low-side power-MOSFET are driven sequentially (i.e. neither MOSFET is on at the same time). During on-time the resonant-tank delivers some energy to the output and stores the remaining energy. When the first power-MOSFET turns-off, there is a period of dead time before the second power-MOSFET turns on. During dead time some of the remaining stored energy in the resonant-tank, continues to circulate current causing the half-bridge voltage to slew towards the next switch. The half-bridge voltage slew continues until either the voltage is clamped by a MOSFET body-diode (ZVS), or the tank runs out of energy (non-ZVS). The goal for the LLC-converter is to always run in ZVS (zero-voltage-switching), operation. This is where the voltage across the next power-MOSFET is close to zero prior to turning on the power-MOSFET. This results in near zero capacitive (COSS) MOSFET losses. After the first power-MOSFET turns-off, the HiperLCS-2 auto-dead time function holds off second power-MOSFET until the controller detects either the end of half-bridge voltage-slew or abnormally reaches maximum dead time. Following this the second power MOSFET will turn-on. The dead time of a given LLC-converter may vary with input voltage and output load. The HiperLCS-2 will automatically adjust dead times in the range from ~90-500 ns.

Frequency Range	Min	Nom	Max	Unit
0	23	90	135	kHz
1	30	120	183	kHz
2	45	180	270	kHz
3	60	240	366	kHz

 
 Table 1.
 Table of Primary and Secondary Frequency Ranges Selections. Primary Device Frequency Range Selection via PP Pin Resistor (see data table). Secondary Device Frequency Range Selection by Part Number.

#### **Primary Protection and Fault Response**

If secondary controller does not wake up within 32 ms of primary switching start, then the power device will declare fault. If hand over to secondary control does not occur within a further 32 ms after secondary wake-up, then the primary will declare a fault. As with all faults, the primary is the master of fault management. When a fault is declared (primary or secondary), the device will go into either latching (off) or non-latching fault handling.

For non-latching faults the primary device will initiate auto-restart. Auto-restart has two responses a short fault response and a long response.

Short fault auto-restart occurs for fault events that are detected while operating in secondary control. This auto-restart off-period is approximately 200 ms. All faults that trigger during primary control result in analog auto-restart response where the off-time is around 5 seconds.

The short-auto-restart event allows quick restart for occasional faults. The long auto-restart ensures that repetitive auto-restart maintains a very low auto-restart-attempt versus auto-restart-off-time ratio. This in turn ensures that the persistent fault does not create excess electrical nor thermal stress on the part.

The primary includes many layers of device self-protection to achieve rugged performance in the event of faults.

At power-up the device completes FMEA checks (failure-mode effect analysis) on device pins. If faults are observed the device will not start switching. Note that such an FMEA fault will not report an error code on the PP pin if it occurs prior to switching. Fault reporting messages on the PP pin are only generated for faults which occur after switching has started.

Primary half-bridge current is internally sensed during low-side MOSFET on-time. This is used for both primary start-up and also for safety current limits during secondary mode.

The primary device also includes (high-side controller) overtemperature protection. This protects against excessive power dissipation in the primary package. The device also has ambient (low-side controller) thermal protection, which prevents restart until the temperature has lowered sufficiently to allow restart. This prevents thermal temperature built up which might otherwise occur in the event of immediate restart for repeat fault conditions. Thermal fault triggers either latching or non-latching response (PP pin select).

The L pin detects input voltage for undervoltage and overvoltage protection. The input voltage is coupled via a resistor connected to L pin. The L pin is polled during burst operation to reduce system consumption. During continuous switching (non-burst) the L pin is continuously monitored. Overvoltage and undervoltage both have hysteresis to prevent chatter. On exiting undervoltage the device goes through a restart. However, for overvoltage the device switching is blocked while the condition persists but allowed to continue when condition is removed. Note: that the L pin detects at power-up whether the pin is connected to ground or if there is a resistor between the HD pin and L pin. If the L pin is connected to ground then the PP pin power-good input function is used instead to indicate line-UV/OV conditions.

The BPL pin provides main supply voltage into the low-side driver and controller. This voltage is internally regulated to provide 5 V at 5VL pin. Note: the 5VL pin is not intended to provide power to any external devices other than the isolation device. The BPH and 5VH pins provide similar functions on the high-side driver. Both must be externally decoupled to ground with a capacitor.

The BPL, 5VL, BPH and 5VH pins are monitored for undervoltage condition. At start-up the device will not begin switching until all are above their respective UV thresholds. The pins are also monitored during normal switching and UV will trigger auto-restart. Please note: that unlike faults, a UV-condition on BPL, 5VL, BPH, 5VH will force a restart but will not output a fault to the PP pin.

#### **Miscellaneous Primary Functions**

At power-up, the PP pin is used to read customer configuration (resistor) settings, which select for the primary start-up frequency range (90, 120, 180, 240 kHz), and latching/non-latching fault handling. The PP pin may also be used to receive a power-good input signal from an external system (such as PFC controller) when the L pin is connected to ground. This same signal could in also be used for remote-on/off. The PP pin can also receive an external fault signal to disable device under fault or other conditions – this signal is handled with latching/non-latching fault response. During fault conditions the PP pin is also used to output device error codes to help with debug. The error code is output as a binary non-return-to-zero (NRZ) bit stream.

Frequency Range	Fault Response
0	Auto-on
1	Auto-on
2	Auto-on
3	Auto-on
0	Latch-off
1	Latch-off
2	Latch-off
3	Latch-off
	0 1 2 3 0 1

 Table 2.
 Table of Primary-Side PP Pin Functionality Selections. See Data Table for PP Pin Selection Resistor Values.

The BM pin is used to signal that the HiperLCS-2 is operating at low-load. Amongst its uses, this signal can be used to turn-on/off an inrush bypass relay. It could also be used to change the set-point of the PFC boost voltage.

The FL pin input is used to receive secondary communications, such as regulation, burst modes and faults. This input receives a digital 0-5 V signal from the FL-output of the isolation device.

#### HiperLCS-2 Secondary-Side Isolation-Device Operation

#### **Communications to Primary-Device**

As mentioned earlier the primary device will autonomously start-up and begin switching, with primary remaining in control until the output voltage reaches close to regulation. At this point the secondary will take control (primary will hand over control to secondary) and all further switching is then controlled from the secondary side controller.

The secondary-device communicates to the primary-device via the FluxLink isolated communications. Communication commands include hand over (i.e. secondary taking control), half-bridge switching, burst mode and declaration of fault condition.

The isolation-device FL-output is connected to the primary FL-input.

#### Secondary Fault Handling

After hand over the secondary remains in control until either: a UV-event occurs (primary or secondary), or until a fault occurs (primary or secondary). Under either of these conditions UV or fault, the control reverts back to primary control. Also under either of these conditions the primary would enter auto-restart. For autorestart, the device has two functionalities, either latch (off-condition), or non-latching (i.e. auto-restart).

After auto-restart off-time, the primary restart is the same as for first power-up as described earlier in primary control section.

Note that the primary is the device which handles all system level fault events. Any secondary fault is reported to the primary and ultimate system level fault response comes from the primary.



#### **Secondary Control**

The secondary takes control of switching as the output voltage approaches regulation. Once in secondary control, the secondary device uses 3 signals to achieve closed loop control. The FB pin signal is coupled via resistor divider from the output voltage. This FB pin voltage represents a scaled version of the output voltage. The FB pin generates an error signal with respect to an internal 3.75 V DC reference. The error signal is output via an OTA, operational trans-conductance (voltage input to current output) amplifier in the form of an error current signal to the CMP pin. The gain of the OTA amplifier is dependent on the magnitude of the error signal. Low gain (e.g. 1x.), is used for small errors, but once error exceeds a threshold the gain is increased to high gain (e.g. 4x.). This non-linear amplification (NLA), allows for extremely fast large-signal transient response.

The CMP pin is coupled to an external resistor capacitor compensation network (two poles one zero). This compensation network is tailored to achieve good phase-gain response. The error current signal is integrated and filtered by the compensation network. When the system is in regulation the error-current-signal should be extremely small, thus a small current causing very small variations in the CMP voltage (compensation network).

The IS pin senses the winding voltage from the transformer. The sense winding is coupled to the primary of the transformer, generating a voltage whose magnitude is similar in scale to that of the main output voltage winding. The IS pin has internal clamping at 2.5 V. The sense winding voltage is AC coupled (via capacitor) and then converted to a current using a resistor into the IS pin. The magnitude of the current is low, below 35  $\mu$ A, thus causing minimal system loss.

Internally the IS pin AC-coupled current signal is compared against the CMP pin voltage. When the two cross this indicates the end of a half-cycle.

The IS pin signal contains, amongst other things, information about primary input current. This means that the overall system implements a current mode control. The control system does not directly control frequency, but instead controls half-cycle by half-cycle in time-domain. However, the frequency is an indirect function of the control loop, thus in steady state the frequency will be stable and a function of resonant tank, input voltage and output power, etc.

PS Pin Selection	Burst Threshold (%)**	Constant Current Compatible	Burst Control
0	10	No	Internal
6	10	Yes	Internal

Table 3. Table of Secondary-Side PS Pin Functionality Selections. Selected via PS Pin Resistor (see data table). \*\*Burst Percentage of Maximum Continuous System Output Power.

#### **Burst Mode**

The CMP pin voltage is inversely proportional to primary input current. This voltage is used to determine when the system should enter burst mode. Thus the burst mode entry point is a function of output power. This function is compensated for input voltage, such that the burst-entry point should be at relatively similar power levels over the entire input voltage range. For the HiperLCS-2 the burst mode is used for more than one reason.

The first reason for burst is to maintain system efficiency. In full frequency mode the system efficiency naturally drops significantly below 10% load. So the first goal is to enter burst mode before 10%. The regulation is achieved by switching less often but continuing to deliver the equivalent of about 10% power per switched half-cycle.

The second goal once in burst is to maintain output regulation. This is achieved using three modes of burst regulation.

The third goal once in burst is to maintain the switching frequency envelope well below the audio resonant frequency of the LLC transformer. The audio/mechanical resonance LLC-transformers, is typically in the 7-12 kHz range. Thus in burst the HiperLCS-2 intends to maintain switching frequency envelope below approximately 1 kHz. Being well below the audio resonance of the transformer means that there will be little or no noise from the transformer.

The fourth goal is to maintain ability to satisfy 0-100% load step without losing regulation.

To help achieve the goals above, the HiperLCS-2 uses 3 modes of operation when in burst.

On entering burst, the highest power burst mode is called intermediate mode (IM-burst). In this mode the system is still in closed loop analog control via the CMP pin. The IM-burst works by forcing off-time at a 1.5 ms repeat period. The IM-mode off-time is terminated once the output voltage decays to a minimum value ( $V_{out}$ MIN). At this point switching begins again and the analog control loop closes to reach regulation. Regulation is then maintained until the off-to-off timer again reaches the 1.5 ms period. Then the next IM-mode off-time begins.

The next level down in terms of output power, is the light-load LL-mode burst. During this mode the CMP is no longer used. Instead an internal VCMP\_BURST is used, where VCMP\_BURST corresponds to the equivalent of 10% load. The LL-mode burst switching begins when output voltage reaches  $V_{out}$ MIN. The switching continues, terminating when output voltage exceeds  $V_{out}$ MAX. The device enters LL-off-time until the voltage again reaches  $V_{out}$ MIN. During the LL-burst switching each half-cycle delivers equal power (determined by internal VCMP\_BURST) and approximately equal to 10% load.

The lowest level of burst in terms of output power is super-light SL-burst. During this mode the switching occurs after a maximum off-time of 50 ms. The start SL-burst switching depends on the 50 ms off-time only. If the output voltage drops as far as V<sub>out</sub>MIN then the device will move back to LL-burst. During SL-burst switch, the burst switches until either it reaches V<sub>out</sub>MAX or reaches 60  $\mu$ s of total switching time.

With the burst modes of the HiperLCS-2 the device is able to achieve exceptional system no-load performance. Unlike other systems though it can still accommodate a full 0-100% load step without dropping out of regulation. The burst mode also intrinsically manages audio noise. The output ripple during burst is also entirely bounded by the V<sub>out</sub>MIN and V<sub>out</sub>MAX of the system. The device achieves 1% system regulation, internally the FB pin V<sub>out</sub>MAX and V<sub>out</sub>MIN thresholds are fixed at ±0.65% of V<sub>out</sub>REG.



#### SR (Synchronous Rectifier) Control

The D1 and D2 pins monitor the drain voltage of the SR MOSFET's. When D1 and D2 go below ground this indicates the potential start of SR conduction. Typically, D1 and D2 pins will have a small series resistor to prevent excessive substrate current when below ground voltage. Under certain conditions, there may be ringing on D1 and D2, and the ring may temporarily go below ground only to rise back above ground. The HiperLCS-2 therefore employs a learning engine to ignore the ringing. Therefore, when the ring-filtered value of D1 (or D2) goes below a turn-on threshold, the associated SR MOSFET is then activated. Once activated the D1 (or D2) signals then monitor the on-state Drain-Source voltage across the SR MOSFET. This gives an indication of conduction current. For an LLC-converter in discontinuous conduction mode (DCM), the rectified output current (i.e. power delivered to the secondary), will reach zero before the end of the half-cycle. In discontinuous mode (DCM) LLC operation, the detected D1 (or D2) will then terminate the SR-conduction when current approaches zero. The secondary controller turns off the SR MOSFET before reverse conduction. For an LLC-converter operating in continuous conduction mode (CCM), the current will not reach zero prior to the end of the half-cycle. Therefore, to prevent reverse SR MOSFET current, the HiperLCS-2 will terminate SRconduction prior to half-bridge switching. This can be done because the half-bridge switching signal is originated at the secondary controller. Thus the secondary control can turn off the SR MOSFET at exactly the latest possible moment to guarantee no shoot-thru in CCM mode. This is something that allows the HiperLCS-2 to safely operate in CCM-mode with maximum SR conduction. Note: that in CCM mode, the primary and secondary rms currents are reduced vs. DCM mode. Therefore, being able to operate in safely in CCM mode generally results in higher system efficiency.

#### SR Driver Voltage Clamp

The G1 and G2 pins respectively drive the SR MOSFET's for each phase of the LLC secondary. The BPS pin voltage supplies drive current to the G1 and G2 gate-drive outputs. However, the BPS pin is able to accommodate a voltage range of up to 24 V. This would exceed the maximum gate withstand for most SR MOSFETs. Also most SR MOSFET's are fully enhanced at voltages well below that. In order to limit the SR-MOSFET gate-charge/discharge energy, the HiperLCS-2 provides an internal voltage clamp to limit the maximum voltage output on the G1 and G2 SR-drive pins. The gate-drive voltage is internally controlled to a maximum of either 11.5 V or 6.5 V. The maximum voltage depends on the selected frequency range of the device. Frequency ranges 0,1 (90, 120 kHz), receive 11.5 V whereas higher frequency ranges 2,3 (180, 240 kHz) receive 6.5 V drive limits. Limiting the SR MOSFET drive voltage limits the gate-charge/discharge losses. Typically, higher frequency SR MOSFET's are structurally optimized to have lower Vgs turn-on thresholds and thus fully enhanced at lower voltages.

#### Layout connections and Recommended Values

During PC-board layout, it is important to understand the current return pin for each signal, so that correct routing paths can be implemented. The following table shows that information along with generic recommended external component values. Obviously for all designs component values may change or be optimized to suit specific conditions, however the recommended values are given as a good starting point.

Isolation Barrier	Device	Pin	Most Sensitive	Returned to Pin	Recommended Value	Notes
Primary Lo	w-Side Co	ntrol				
Primary	LCS726x	BM		GP		
Primary	LCS726x	BPL		GD	$\begin{array}{c} 1 \ \mu\text{F} \ / \ 35 \ \text{V} \ \text{SMD} \ \text{right} \\ \text{at pin. Usually also} \\ 47 \ \mu\text{F} \ \text{further from} \\ pin \end{array}$	The gate-drive energy comes from this pin. Large BPL pin capacitance will also be needed away from pin
Primary	LCS726x	5VL		GP	1 μF / 10 V SMD right at pin	
Primary	LCS726x	FL	**	GP (LSR2000 device)		There is a connection from isolation device LSR2000 to LCS726x. The 5VL, GP and FL pins of both devices should be directly connected
Primary	LCS726x	PP		GP	RPP at pin	See data table for selection values
Primary	LCS726x	L	**	GP	4 MΩ	Split resistance into at least 3 SMD resistors. Ensure that all resistor are located close to L pin
Primary Hig	gh-Side Co	ontrol				
Primary	LCS726x	BPH		НВ	$1~\mu\text{F}$ / 35 V SMD right at pin. Usually also $10~\mu\text{F}$ further from pin	
Primary	LCS726x	5VH		HB	220 nF / 10 V SMD right at pin	
Primary	LCS726x	Heat Sink		S		If heat sink used ensure that it is grounded to S pin



Isolation Barrier	Device	Pin	Most Sensitive	Returned to Pin	Recommended Value	Notes
Primary Flu	ıxLink					
Primary	LSR2000	5VL		GP(LSR2000)		There is a connection from isolation device LSR2000 to LCS726x. The 5VL, GP and FL pins of both devices should be directly connected
Primary	LSR2000	GP		GP(LCS726x)		There is a connection from isolation device LSR2000 to LCS726x. The 5VL, GP and FL pins of both devices should be directly connected
Primary	LSR2000	FL	**	GP(LCS726x)		There is a connection from isolation device LSR2000 to LCS726x. The 5VL, GP and FL pins of both devices should be directly connected
Secondary	Control					
Secondary	LSR2000	D1	**	GSA	499 ohm	Switch signal hence pay attention to layout/coupling
Secondary	LSR2000	D2	**	GSA	499 ohm	Switch signal hence pay attention to layout/coupling
Secondary	LSR2000	G1		GSA	4.7 ohm	High current gate-drive. Wider PC-board trace to limit inductance
Secondary	LSR2000	G2		GSA	4.7 ohm	High current gate-drive. Wider PC-board trace to limit inductance
Secondary	LSR2000	BPS		GSA	1 μF / 35 V SMD right at pin. Usually also 47 μF further from pin	
Secondary	LSR2000	5VS		GSB	10 μF / 10 V SMD right at pin	Note: this pin also has high internal current spikes, hence larger capacitor right at the pin
Secondary	LSR2000	IS	**	GSB	RIS resistor + 470 pF / 200 V capacitor	Note: the RIS resistor is typically split into two series resistors to share the voltage rating. Series resistors are placed as close as possible to the IS pin to limit external noise coupling
Secondary	LSR2000	CMP		GSB	Initial values (150k + 2.2 nF) // 100 pF. All components at pin	Compensation components may require modification to optimize phase-gain response
Secondary	LSR2000	FB	**	GSB	10 k lower resistor value, at pin	The resistor divider 10 k $\Omega$ low-side resistor is used to give a good balance between no-load consumption and noise rejection. Lower values will give more noise immunity, but will also increase no-load consumption.
Secondary	LSR2000	PS		GSB	RPS at pin	See data table for selection values

Table 4. Data Sheet Body Table.

## **Basic Layout Guidelines**

The HiperLCS-2 is a high-frequency power device and requires careful attention to circuit board layout in order to achieve maximum performance. The bypass capacitors need to be positioned and laid out carefully to minimize trace lengths to the pins they serve. Surface mount (SMD) components are recommended for minimum component and PC-board stray inductance.

The HiperLCS-2 has several sensitive pins, used for sensing analog signals. Good device performance can be achieved by paying special attention to the layout at and around these pins.

On the primary-side control, both the FL pin and L pin have may be sensitive to layout.

The FL pin output is essentially a digital output, so for this pin the issue is to ensure that the GP, FL and 5VL are all directly connected between the primary and isolation devices. If the grounding is not done correctly this can lead to potential noise pickup.

For the L pin this is a sensitive analog input pin. The L pin senses input voltage via a resistor (typically 4 M $\Omega$ ). The resistor is typically made of a series of SMD resistors. Splitting the resistance into several devices will minimize the voltage stress on each resistor. There are two different examples of how to connect the L pin to VIN. The first (incorrect) would be to place all the resistors close to VIN and then run a long PC-board trace to the L pin. This is incorrect since the node from resistor to L pin is high-impedance and a long PC-board trace would allow noise pickup injected into the L pin. The second (correct) method would be to place ALL the resistors close to



the L pin and run a long PC-board trace to VIN. This method is correct since the node from resistor to VIN is very low-impedance and thus very unlikely to pick-up noise. On the secondary-side control, the FB, CMP, IS and D1/D2 pins may be sensitive to layout.

The FB pin is a high impedance voltage input pin. It is connected to  $V_{\text{OUT}}$  via a resistor divider ( $R_{\text{UPPER}}, R_{\text{LOWER}}$ ).  $V_{\text{OUT}}$  is a low-impedence node, so this may be the long PC-board connection. The node from  $R_{\text{UPPER}}$  to  $R_{\text{LOWER}}$  is high impedance and should be placed as close and tightly coupled as possible to the FB and GSB pins. The general recommendation for  $R_{\text{LOWER}}$  is 10 k $\Omega$ , which is a good compromise between no-load consumption and noise immunity. Further reducing  $R_{\text{LOWER}}$  would increase noise immunity but increase no-load consumption. Note that any noise injected into the FB pin could be observed as duty-cycle and/or frequency variation.

The CMP pin is a high impedance current output and voltage-input pin. The compensation network of one-resistor and two capacitors is should be place as closely and tightly coupled as possible to the CMP and GSB pins. Any noise injected to the CMP pin could be observed as duty-cycle and/or frequency variation.

The IS pin is a current input, with a forced voltage on the pin. The IS pin signal passes from the winding-sense pin of the transformer through series capacitor CIS and resistor RIS connected to the IS pin. The transformer winding signal pin should first be connected to the CIS capacitor and then in series to the RIS resistor. The RIS resistor should be split into two SMD resistors, the last of which should be terminated right at the IS pin of the HiperLCS-2 device. The transformer should have both a winding sense signal pin and also a winding-sense small signal ground pin. The winding sense small signal transformer ground pin should be connected to the GSB pin of the HiperLCS-2. The winding sense transformer signal pin is a low-impedance node and therefore this may be the long PC-board connection. This trace however is carrying a large magnitude (medium voltage) AC coupled signal. Thus care needs to be taken to keep these signals away from other small signal sensitive inputs of the device.

The D1/D2 pins are both high impedance voltage inputs. The D1/D2 are connected via a low-value resistor (typically 499  $\Omega$ ), to the respective Drain of the SR MOSFET with respect to GSA pin. The SR MOSFET Drain point is a low-impedance node so may be the long PC-board connection. This trace however is carrying a large magnitude (medium voltage) AC coupled signal. Thus care needs to be taken to keep these signals away from other small signal sensitive inputs of the device.

Transformer T1 is a source of both high di/dt signals and dv/dt noise. The high di/dt can couple magnetically (PC-board loop signal loop area coupling), to sensitive circuitry. The high dv/dt inject noise via electrostatic (stray capacitive), coupling. Electrostatic noise coupling can be reduced by grounding the transformer core, but it is not economically feasible to reduce the stray magnetic field around the transformer without drastically reducing its efficiency. Where possible, sensitive signal paths and components should be located away from the transformer to avoid noise pickup. The secondary transformer main output windings should be twisted together prior to winding. Twisting the wires together will minimize differences in secondary leakage and will enhance current balance between the windings. Also as importantly please ensure that all secondary wires are twisted together prior to termination on the transformer pin. Twisting the terminate wires will minimize wire-loop area and minimize the ability of the windings to couple stray flux to other system signals.

HiperLCS-2 primary-side power pins are the S, HB and HD pins. Unlike some designs, the HiperLCS-2 is intended for use with only a single resonant capacitor. This is typically connected to primaryreturn (primary ground). The HB pin is connected to the LLC transformer and the transformer to the resonant capacitor, this path length of PC-board connection should be minimized. Care should be taken to minimize return path (primary-ground) between the resonant capacitor and S pin of the HiperLCS-2 and the PC-board connection between resonant capacitor and device. The HD pin connection should also include a local decoupling capacitor from HD to primary ground (S pin potential). The goal of the local decoupling capacitor is to reduce the path length for high magnitude switched currents.

Primary-side power ground (i.e. local decoupling capacitor ground, S pin, resonant capacitor ground), should all have an independent and direct PC-board trace back to the bulk-capacitor ground. Primary- side small signal ground. This is the node shared by primary GP pin, isolation device GP pin, BPL pin capacitor(s) ground, transformer primary bias ground pin, primary bias capacitor(s) ground. All of these devices should be kelvin connected to this ground. The ground should then have a single direct PC-board trace back to the primary bulk-capacitor ground.

#### Note:

HiperLCS-2 Secondary-side only has one power pin and this is the GSA pin. The GSA pin should be tightly connected to the SOURCE of both SR MOSFET's (SR1 and SR2). Both SR MOSFET's should be co-located as close as possible with a shared Source connection point. The GSA pin should be connected at the mid-point between SR1 and SR2 SOURCE pin connections. The G1 and G2 secondary gate-driver pins do drive substantial gate current and so should be kept to a short (and equal) length(s). The D1 and D2 DRAIN sense pins, should also be kept to equal lengths. The location of the GSA pin connection to SR MOSFET source, will determine the accuracy of D1/D2 detection. This can effect the current-sensed turn-off point for SR1 and SR2 when operating in DCM (discontinuous) mode. If fine tuning is required, moving the GSA connection point closer to one of the two MOSFET's can change the relative turn-off points for SR1 and SR2. Also fine tuning of both turn-off points can be achieved by changing the resistor ( $R_{D1}$  or  $R_{D2}$ ), in series with D1 or D2 pins. The resistor is typically 499  $\Omega$ , but may be adjusted in the range 250 –  $1 \text{ k}\Omega$ . These small changes will adjust the turn-off current of SR1 or SR2 (larger resistor increases current at which SR will turn-off).

#### **Key Design Details**

The LLC can be optimized for different criteria. The HiperLCS-2 has four frequency ranges of operation with nominal frequencies of 90, 120, 180, 240 kHz. For highest possible efficiency, lower frequency designs generally give marginally better results. However high frequency designs are very close in efficiency. Also high-frequency design will yield smaller magnetic size and smaller resonant capacitor. For most designs litz wire is recommended. For a given design the optimal diameter and number of strands is automatically calculated by Power Integrations design tools (PIXIS HiperLCS-2 Spreadsheet), that assist with the entire design process.

For most designs low-loss ferrite cores lower the magnetizing losses and a recommended for best efficiency. Likewise, the maximum flux-density also has strong effect on hysteretic magnetic losses. Lowering maximum flux-density (i.e. increasing secondary turns), can often give a higher efficiency design (especially at higher frequencies).

For nominal input voltage and 100% load, it is recommended that the magnetizing inductance ( $L_{_M}$ ) is adjusted to give a half-bridge slew rate of approximately 250 ns at 380 VDC. Such a design should achieve ZVS operation for all load and input voltage conditions. Lowering the



magnetizing inductance beyond this target, will result in higher circulating currents and higher resistive losses. For all HiperLCS-2 designs, the goal is for the resonant tank to still be able to achieve ZVS operation at the  $F_{MAX}$  limit for the chosen frequency range. This is important since when the converter sees a load transient (when load is say stepped to zero), the frequency may temporarily reach  $F_{MAX}$  limit prior to entering burst mode. For this reason, it is important to choose the frequency range that offers the appropriate range of frequencies needed for the operational scope of the converter. Note the  $F_{MIN}$  limit of the chosen frequency range will become active at lowest input voltage and highest load. Typically, the  $F_{MIN}$  limit is only reached under fault conditions.

The resonant inductance  $\rm L_{\rm RES}$  (or often referred to as leakage inductance), should be designed to provide maximum overload power.

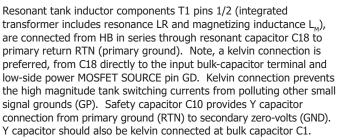
For the HiperLCS-2, it is recommended that the design be optimized for operation at resonance, CRM at nominal input voltage and 50% load. At higher input voltages the converter may enter continuous mode, CCM operation. For some converters this may present a risk of shoot-through but the HiperLCS-2 is uniquely designed to allow the system to enter continuous conduction mode, CCM without risk of shoot-through or other anti-social converter behavior.

## **LLC Primary Schematic**

The HiperLCS-2 receives a rectified and filtered DC input bus voltage ( $V_{\text{BULK+}}$ ). The input bus voltage is sensed via three series resistors R24, R25, R26 connected in series to the L pin. An external PFC power-good signal may be connected via resistor R1 to the PP pin. Primary-side detected output overvoltage is sensed at the primary bias-winding (T1-5/6), via Zener diode VR1 and resistor R34. This OVP signal is then coupled to the PP pin via resistor R32 and transistor Q3. When Zener VR1 conducts, current will be pulled from PP pin to ground via transistor Q3. Resistor R33 selects the PP pin programming (primary frequency range and fault-response). The BM pin may be coupled to an external circuit which could drive an in-rush relay and/or change PFC voltage as a function (BM becomes active during burst mode).

The 5VL and BPL pins are decoupled by capacitors C24 and C22 respectively. Diode D6 rectifies primary bias winding voltage (T1 pin 5) and decouples to capacitor C27, the voltage is fed through resistor R31 to decoupling capacitor C21. Before switching during start-up, charge bias current is provided from the BPL pin and out to capacitor C21 via resistor R30. Capacitor C21 is also available to supply start-up bias to external PFC stage. Resistor R30 limits output current from BPL in the event of a large current draw from external PFC stage. During normal operation the bias current comes from the bias winding to capacitor C21. In the event of high bias-winding voltage, resistor R31 limits the shunt-current that may be consumed by the BPL pin when clamping BPL internally to ground via shunt regulation. Note that the bias winding voltage may vary over a 25% range from zero to full output load. For best no-load performance, the bias winding is intended to deliver a minimum of 15 V to the bias winding at zero load conditions, while the BPL pin shunt will engage if the bias winding grossly exceeds 21 V.

In normal switching, during the low-side power MOSFET-on period the high-side bootstrap is charged via diode D4 and resistor R23 into capacitor C6. Resistor R23 limits the current into capacitor C6 in the event that the capacitor voltage is fully depleted. Since the C6 charge current flows through the low-side power MOSFET, the removal of resistor R23 may under worst-case conditions result in trigging of low-side safety current limit. Resistor R22 and capacitor C17 provide further filtering of high-frequency ripple. The high-side 5VH is decoupled via capacitor C19. Note that all high-side decoupling is with reference to HB potential.



## LLC Secondary Schematic

Transformer output pins T1 FL3/FL4 provide the positive output voltage which is rectified and filtered by capacitors C27, C28, C30, C31 and C32. These capacitors must combine to provide low ESR which mostly defines the output ripple of the system. Also the combined C-value total of these capacitors should be chosen to match the desired burst threshold. These capacitors are decoupled to secondary ground (GND). Transformer output pins T1 FL1/FL2 are the return path rectified via synchronous rectifier MOSFETs Q4 and Q5 to secondary ground. The secondary power path is from T1 FL3/FL4 through C27, C28, C30, C31, C32 and returning via Q4, Q5 to transformer T1 FL1/FL2. This secondary power path should be kept as short and symmetrical as possible between each of the two phases of the LLC and the layout should use wide high current traces.

The LSR2000C (U3) is decoupled at 5VS and BPS pins by capacitors C9 and C33/C34. The secondary bias winding T1 pin 12 is rectified via diode D7 and filtered by capacitor C33/C34. At no-load the secondary bias voltage may drop to a lower voltage and additional no-load bias comes from output voltage (+24 V) via resistor R30 and Zener diode VR1. Output voltage is sensed via resistor bridge R36 and R37 with local capacitor decoupling C29 to remove any high-frequency noise.

Compensation is provided between CMP and GSB, via components R44/C36 which provide a pole and zero and C35 which adds another pole. These compensation component values provide a good starting point for most designs. The transformer IS winding T1/9, provides a medium voltage signal which is capacitor coupled via C37 and then via resistors R48, R49 to the IS pin. The IS signal is a sensitive high-frequency analog signal and so care should be taken with layout, to keep capacitor C37 away from the IS pin to reduce stray capacitive coupling, but the resistor R48 should be terminated at the IS pin for best noise immunity. The IS winding a scaled sum of primary winding inductance ( $L_R + L_M$ ) voltages.

The D1/D2 pins sense the synchronous rectifier (Q4, Q5), drain voltages via resistors R40, R45. The resistors are required to limit below-ground current into the D1, D2 pins. The minimum value of R40, R45 should be 200 ohms, but these resistor values can be increased 2x to 5x to offer adjustment to SR turn-off threshold. Increasing resistor R40 and R45 values will cause SR to turn off at higher SR current. Alternately put, increasing resistor R40 and R45 values will cause SR to turn off early in the conduction cycle.

Synchronous MOSFET Q4, Q5 drive is coupled from G1/G2 pins via resistors R39, R43. The drive resistors are optional and intended to limit super high-frequency MOSFET drive ring. Local pull-down resistors R38, R42 are present to ensure the MOSFET Q4, Q5 remain off in the FMEA case where gate-drive is absent for some reason.

The PS pin resistor R50 selects secondary-side user functions (such as CV or CC mode, etc.).



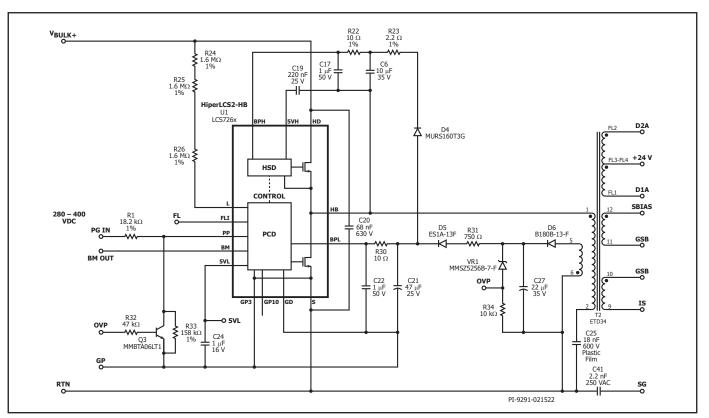
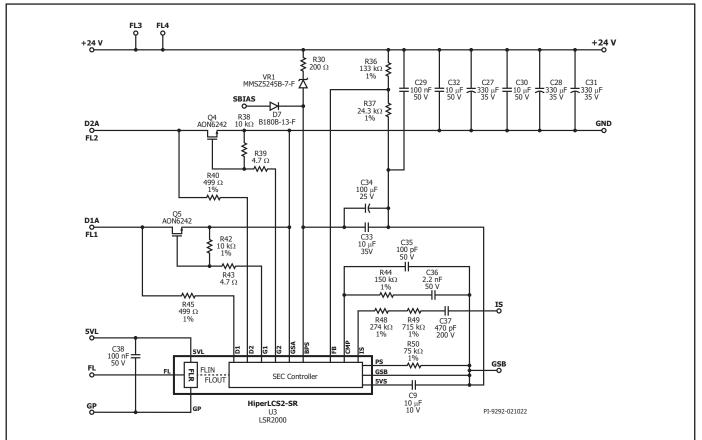
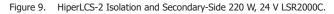


Figure 8. HiperLCS-2 Primary-Side 220 W, 24 V LCS726xC.







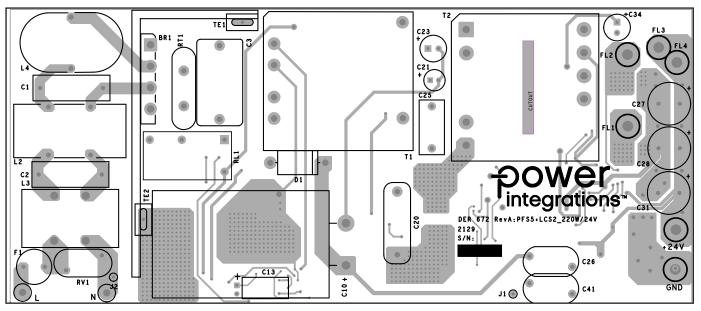


Figure 10. PCB Layout (Top View).

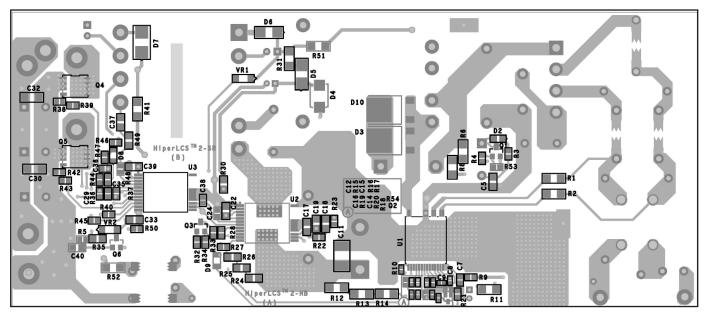


Figure 11. PCB Layout (Bottom View).



#### Absolute Maximum Ratings<sup>1,2</sup> – LCS726xC

-	
HD Pin Voltage <sup>2</sup>	
DC Output Current <sup>4,5</sup> :	
LCS7260C	
LCS7262C5.8 A	
LCS7265C 10.9 A	
BPH Pin Voltage <sup>3,5</sup> 0.3 V to 27 V	
BPL Pin Voltage <sup>5</sup> 0.3 V to 27 V	
BPL Pin Current	
5VH Pin Voltage <sup>3</sup> 0.3 to 6 V	
5VL Pin Voltage0.3 to 6 V	
FL, PP Pin Voltage0.3 to 6 V	
BM Pin Voltage0.3 to 6 V	
BM Pin Current	
L Pin Voltage0.3 V to 600 V	
L Pin Current	
S Pin to GP or GD Pin Voltage±0.33 V	
Junction Temperature <sup>5</sup> :	
FREDFET40 °C to 160 °C	
Driver40 °C to 150 °C	
Storage Temperature65 °C to 150 °C	
Ambient Temperature40 °C to 105 °C	
Lead Temperature <sup>4</sup>	

V Notes:

- 2. All voltages referenced to low-side Source S and signal ground GP, GD except noted otherwise,  $T_A = 25$  °C.
- 3. Referenced to Half-bridge Connection HB,  $T_{A} = 25$  °C.
- 4. Continuous DC output current per FREDFET calculated at 25 °C case and 125 °C junction temperature.
- 5. Normally limited by internal circuitry.

#### **Thermal Resistance**

Thermal Resistance: InSOP-24C Package

LCS7260 (θ <sub>14</sub> )	74 °C/W <sup>1</sup> , 59 °C/W <sup>2</sup>
LCS7262 (θ <sub>14</sub> )	
	63 °C/W <sup>1</sup> , 51 °C/W <sup>2</sup>

#### Notes:

- 1. Individual exposed pad (HB or HD), soldered to 0.36 sq. in. (232 mm<sup>2</sup>), 2 oz. (610 g/m<sup>2</sup>) copper clad.
- Individual exposed pad (HB or HD), soldered to 1.0 sq. in. (645 mm<sup>2</sup>), 2 oz. (610 g/m<sup>2</sup>) copper clad.



<sup>1.</sup> Maximum ratings specified may be applied one at a time without causing permanent damage to the product. Exposure to Absolute Maximum Ratings conditions for extended periods of time may affect product reliability.

Parameter	Symbol	Conditions $T_{JC} = 0 \text{ °C to } 100 \text{ °C}$ BP = BPH = 18  V (Unless Otherwise Specified)	Min	Тур	Max	Units
Primary High-Side Contro BPH Pin	ller/Driver		I	1	1	
BPH-HB Undervoltage Start Threshold	V <sub>BPH(UV+)</sub>		12.4	13.2	14	V
BPH-HB Undervoltage Stop Threshold	V <sub>BPH(UV-)</sub>		10.15	10.8	11.3	V
BPH-HB Start/Stop Hysteresis	V <sub>BPH(UV)(HYST)</sub>			2.4		V
BPH (HD) Charge Output Current	I <sub>BPH(CH)</sub>			-1.3		mA
BPH-HB UV to Shunt Spacing	V <sub>BPH(SHGAP)</sub>	See Note D		9		V
BPH-HB Shunt Onset Voltage	V <sub>BPH(SHON)</sub>	$I_{\text{BPHSH}} = 5 \text{ mA}$	23.5	24.5	26.5	V
BPH-HB Shunt Max Voltage	V <sub>BPH(SHMX)</sub>	$I_{\rm BPHSH}={\rm Max}$	23.7	24.7	26.5	V
BPH Shunt Current	I <sub>BPH(SH)</sub>		0		26	mA
		F <sub>sw</sub> = 208 kHz LCS7260C	1.4	1.7	2.0	mA
BPH Pin Current Consumption Switching	I <sub>BPH(SW)</sub>	F <sub>sw</sub> = 208 kHz LCS7262C	1.9	2.2	2.5	mA
		F <sub>sw</sub> = 208 kHz LCS7265C	3.0	3.3	3.6	mA
BPH Pin Current Non- Switching Consumption	I <sub>BPH(NSW)</sub>	No switching $V_{BPH} > V_{BPH(UV+)}$	90	115	150	μA
5VH Pin				1	1	1
5VH-HB Power-Up Threshold	V <sub>5VH(UV+)</sub>	See Note A	4.85	4.9	4.99	V
5VH-HB Power-Up Threshold	V <sub>5VH(UV-)</sub>	See Note A	4.45	4.55	4.7	V
5VH-HB Power-Up Hysteresis	V <sub>5VH(UV)(HYST)</sub>	See Note A	0.3	0.35	0.4	V
5VH-HB Output Voltage	V <sub>5VH</sub>	$I_{\text{svh}} = 0 \text{ mA}$		5.17		V
Primary Low-Side Contro BPL Pin	ller/Driver					
BPL Undervoltage Start Threshold	V <sub>BPL(UV+)</sub>		13	13.7	14.3	V
BPL Undervoltage Stop Threshold	V <sub>BPL(UV-)</sub>		10.4	11.4	12	V
BPL Start/Stop Hysteresis	V <sub>BPL(UV)(HYST)</sub>			2.3		V
BPL (HD) Low Charge Current	I <sub>BPL(CH)LO</sub>	$V_{_{HB}} = 50 \text{ V}, V_{_{BP}} = 0 \text{ V}$	-2.2	-1.9	-1.55	mA
BPL (HD) Charge Output Current	I <sub>BPL(CH)</sub>	$V_{_{HB}} = 50 \text{ V}, V_{_{BP}} = 10 \text{ V}$	-10	-7.7	-4.2	mA

Parameter	Symbol	Conditions $T_{JC} = 0 \text{ °C to } 100 \text{ °C}$ BP = BPH = 18  V (Unless Otherwise Specified)	Min	Тур	Max	Units
Primary Low-Side Control	ler/Driver (cont	.)				
BPL UV to Shunt Spacing	V <sub>BPL(SHGAP)</sub>	See Note D		9		V
BPL Shunt Onset Voltage	V <sub>BPL(SHON)</sub>	$I_{\text{BPLSH}} = 0 \text{ mA}$	20.6	21.6	22.6	V
BPL Shunt Max Voltage	V <sub>BPL(SHMX)</sub>	I <sub>BPLSH</sub> = 26 mA	20.6	21.6	22.6	V
		F <sub>sw</sub> = 208 kHz, LCS7260C	2.4	2.7	3.2	mA
BPL Pin Current Switching Consumption	I <sub>BPL(SW)</sub>	F <sub>sw</sub> = 208 kHz, LCS7262C	3	3.3	3.6	mA
Switching consumption		F <sub>sw</sub> = 208 kHz, LCS7265C	4.1	4.5	5.0	mA
BPL Pin Current Non- Switching Consumption	I <sub>BPL(NSW)</sub>	No switching $V_{\rm BPL} > V_{\rm BPL(UV+)}$	600	780	950	μΑ
5VL Pin						
5VL Power-Up Threshold	V <sub>5VL(UV+)</sub>	C5VL = 1 $\mu$ F / 10 V ceramic See Note A	4.85	4.9	4.99	V
5VL Power-Up Threshold	V <sub>5VL(UV-)</sub>	$C5VL = 1 \ \mu F \ / \ 10 \ V \ ceramic \\ See \ Note \ A$	4.45	4.55	4.70	V
5VL Power-Up Threshold	V <sub>5VL(HYST)</sub>	$C5VL = 1 \ \mu F / 10 \ V \ ceramic \\ See \ Note \ A$	0.30	0.35	0.40	V
5VL Output Voltage	V <sub>5VL</sub>	I <sub>svL</sub> = 0 mA		5.15		V
BM Pin	, I			1	1	1
BM – On Trigger Period (no FL)	T <sub>BM(ON)</sub>	See Note A		5		ms
BM – On Trigger Debounce	T <sub>BM(DB)</sub>	See Note A		5		sec
BM – Off Trigger Period (FL present)	T <sub>BM(OFF)</sub>	See Note A		2		ms
BM – Current Source	I <sub>BM(SRC)</sub>	BM Driving High, V <sub>BM</sub> = 0 V See Note A, C		-19		mA
BM – Current Sink	I <sub>BM(SNK)</sub>	BM Driving Low, $V_{BM} = V_{SVL}$ See Note A		24		mA
BM – On-Output Voltage	V <sub>BM(ON)</sub>	I <sub>BM</sub> = - 2 mA	4.2	4.65		V
BM – Off-Output Voltage	V <sub>BM(OFF)</sub>	$I_{BM} = + 2 \text{ mA}$		0.005	0.1	V
FL Pin	· /			I	I	1
FL – logic 1 Input High-Voltage	V <sub>FL(IH)</sub>			3.2	3.5	V
FL – logic 0 Input Low-Voltage	V <sub>FL(IL)</sub>		1.2	1.5		V



Parameter	Symbol	Conditions $T_{JC} = 0 \text{ °C to } 100 \text{ °C}$ BP = BPH = 18  V (Unless Otherwise Specified)	Min	Тур	Max	Units
Primary Low-Side Contro	ller/Driver (con	t.)				
L Pin Breakdown Voltage	V <sub>L(BV)</sub>	L Pin Disabled (Burst Off-State)	600			V
L Pin UV Stop Threshold Current	I <sub>L(UV-)</sub>		44	49	54	μΑ
L Pin UV Start Threshold Current	I <sub>L(UV+)</sub>		58	63.5	69	μΑ
L Pin OV Start Threshold Current	I <sub>L(OV-)</sub>		98	108	118	μA
L Pin OV Stop Threshold Current	I <sub>L(OV+)</sub>		110	123	135	μΑ
L Pin UV Hysteresis Current	I <sub>L(UV)(HYST)</sub>		12.0	14.6	17.2	
L Pin OV Hysteresis Current	I <sub>l(ov)(hyst)</sub>		12.5	15.2	18.2	
L Pin Sink Current	I <sub>L(SNK)</sub>	See Note A, C	200			μA
- Pin Sink Voltage JV Stop	V <sub>L(SNK)(UV-)</sub>	$I_{\rm L(SNK)} = I_{\rm L(UV-)}$		1.6		V
L Pin Sink Voltage UV Start	V <sub>L(SNK)(UV+)</sub>	$I_{L(SNK)} = I_{L(UV+)}$		1.7		V
L Pin Sink Voltage DV Start	V <sub>L(SNK)(OV-)</sub>	$I_{\text{L(SNK)}} = I_{\text{L(OV-)}}$		2.0		V
L Pin Sink Voltage DV Stop	V <sub>L(SNK)(OV+)</sub>	$I_{L(SNK)} = I_{L(OV+)}$		2.1		V
PP Pin	1			1	1	1
PP Pin Remote-Off Threshold	I <sub>PP(REM-)</sub>		-47	-39	-32	μΑ
PP Pin Remote-On Threshold	$\mathbf{I}_{PP(REM+)}$		-17	-13.5	-10	μA
PP Pin Remote-On/Off Hysteresis	$\mathbf{I}_{_{PP(REM)(HYST)}}$		20	25.5	31	μA
PP Pin Remote-On Voltage	V <sub>PP(REM+)</sub>			0.86		v
PP Pin Remote-Off Voltage	V <sub>PP(REM-)</sub>			0.81		V
PP Pin Fault Clear Threshold	I <sub>pp(FLT-)</sub>		-95	-81	-68	μΑ
PP Pin Fault Assert Threshold	I <sub>PP(FLT+)</sub>		-93	-79	-66	μΑ
PP Pin Remote-On/Off Hysteresis	I <sub>PP(FLT)(HYST)</sub>			1		μΑ
PP Pin Fault Assert Voltage	V <sub>PP(FLT+)</sub>			0.75		v

Parameter	Symbol	<b>Conditions</b> $T_{JC} = 0 \text{ °C to } 100 \text{ °C}$ BP = BPH = 18  V (Unless Otherwise Specified)	Min	Тур	Max	Units
Primary Low-Side Control	ller/Driver (co	nt.)				1
PP Pin Selection0 Resistor	$R_{PP(SEL0)}$	Required Resistor 1% E96 series		59		kΩ
PP Pin Selection1 Resistor	$R_{PP(SEL1)}$	Required Resistor 1% E96 series		158		kΩ
PP Pin Selection2 Resistor	R <sub>PP(SEL2)</sub>	Required Resistor 1% E96 series		226		kΩ
PP Pin Selection3 Resistor	R <sub>PP(SEL3)</sub>	Required Resistor 1% E96 series		316		kΩ
PP Pin Selection4 Resistor	R <sub>PP(SEL4)</sub>	Required Resistor 1% E96 series		412		kΩ
PP Pin Selection5 Resistor	R <sub>pp(Sel5)</sub>	Required Resistor 1% E96 series		536		kΩ
PP Pin Selection6 Resistor	$R_{PP(SEL6)}$	Required Resistor 1% E96 series		715		kΩ
PP Pin Selection7 Resistor	$R_{_{PP(SEL7)}}$	Required Resistor 1% E96 series		1020		kΩ
HB MOSFET						
HB-S Breakdown /oltage Rating	V <sub>HBS(BV)</sub>		600			V
HB-S Reverse Voltage Rating	$V_{\rm HBS(BV)}$	See Note A	-1.5			V
HB Start-Up PreCharge Current to S Pin	$\mathrm{I}_{\mathrm{HB(PRE)}}$			2		mA
	_	LCS7260 $I_{\rm HB}$ = 0.8 A, $T_{\rm _{JS}}$ = 25 °C, 400 $\mu s$ Single Pulse		1.49		Ω
HB R <sub>ds(on)</sub>	R <sub>ds(on)</sub>	LCS7262 $I_{\rm HB}$ = 1.6 A, $T_{\rm _{JS}}$ = 25 °C, 400 $\mu s$ Single Pulse		0.73		Ω
		LCS7265 $I_{\rm HB}$ = 3.2 A, $T_{\rm JS}$ = 25 °C, 400 $\mu s$ Single Pulse		0.41		Ω
	_	LCS7260, $V_{GS} = 0 \text{ V}, \text{ V}_{D}\text{S} = 25 - 480 \text{ V}, \text{ See Note D}$		124		pF
Combined HB C <sub>oss</sub> Effective (0 480 VDC)	C <sub>OSS(EFF)</sub>	LCS7262, $V_{GS}$ = 0 V, $V_{DS}$ = 25 - 480 V, See Note D		248		pF
		LCS7265, $V_{GS}$ = 0 V, $V_{DS}$ = 25 - 480 V, See Note D		460		pF
		LCS7260, See Note C		2.7		A
HB Safety Current Limit	I <sub>HB(SFTY)</sub>	LCS7262, See Note C		5.4		A
	-	LCS7265, See Note C		10.1		A
		LCS7260, See Note C		1.9		A
HB Start-Up Current Limit	I <sub>hb(iovl)</sub>	LCS7262, See Note C		3.7		A
		LCS7265, See Note C		7.0		A



Parameter	Symbol	Conditions $T_{JC} = 0 \text{ °C to } 100 \text{ °C}$ BP = BPH = 18  V (Unless Otherwise Specified)	Min	Тур	Max	Units
Primary Low-Side Cont	troller/Driver (co	ont.)		1	1	
HB Diode				1		1
		LCS7260, IF = 1.0 A, $V_{GS}$ = 0 V, $T_{J}$ = 100 °C See Note D		1.13		V
HB Diode Forward Voltage	V <sub>HB(F)</sub>	LCS7262, IF = 1.0 A, $V_{GS}$ = 0 V, $T_{J}$ = 100 °C See Note D		0.9		V
		LCS7265, IF = 1.0 A, $V_{GS}$ = 0 V, $T_{J}$ = 100 °C See Note D		0.8		V
HB Diode Reverse Recovery Current		LCS7260, IF = $I_{\rm HB(RRM)}$ A, di/dt = 200 A/µs, $V_{\rm R}$ = 400 V, $T_{\rm J}$ = 125 °C		4.0		A
	I <sub>hb(rrm)</sub>	LCS7262, IF = I <sub>HB(RRM)</sub> A, di/dt = 200 A/µs, V <sub>R</sub> = 400 V, T <sub>J</sub> = 125 °C See Note D		5.6		A
		LCS7265, IF = I <sub>HB(RRM)</sub> A, di/dt = 200 A/µs, V <sub>R</sub> = 400 V, T <sub>J</sub> = 125 °C See Note D		8		A
		LCS7260, IF = I <sub>HB(RRM)</sub> A, di/dt = 200 A/µs, V <sub>R</sub> = 400 V, T <sub>J</sub> = 125 °C See Note D		110		ns
HB Diode Reverse Recovery Time	T <sub>HB(RR)</sub>	LCS7262, IF = I <sub>HB(RRM)</sub> A, di/dt = 200 A/µs, V <sub>R</sub> = 400 V, T <sub>J</sub> = 125 °C See Note D		170		ns
		LCS7265, IF = I <sub>HB(RRM)</sub> A, di/dt = 200 A/µs, V <sub>R</sub> = 400 V, T <sub>J</sub> = 125 °C See Note D		200		ns
HB Diode Reverse Recovery Charge		LCS7260, IF = $I_{\rm HB(RRM)}$ A, di/dt = 200 A/µs, $V_{\rm R}$ = 400 V, $T_{\rm J}$ = 125 °C See Note D		220		nC
	Q <sub>hb(rr)</sub>	LCS7262, IF = I <sub>HB(RRM)</sub> A, di/dt = 200 A/µs, V <sub>R</sub> = 400 V, T <sub>J</sub> = 125 °C See Note D		480		nC
		LCS7265, IF = I <sub>HB(RRM)</sub> A, di/dt = 200 A/µs, V <sub>R</sub> = 400 V, T <sub>J</sub> = 125 °C See Note D		840		nC



Parameter	Symbol	<b>Conditions</b> T <sub>JC</sub> = 0 °C to 100 °C BP = BPH = 18 V (Unless Otherwise Specified)	Min	Тур	Max	Units
Primary Low-Side Contro	ller/Driver (co					
HD Pin						
HD-S Breakdown Voltage	V <sub>HDS(BV)</sub>		600			
HD-HB Breakdown Voltage Rating	V <sub>HBHD(BV)</sub>		600			V
HD-HB Reverse Voltage Rating	V <sub>HBS(BV)</sub>	See Note A	-1.5			V
Half-Bridge Over-Temperature Stop	HB <sub>(OT)(STOP)</sub>	See Note A	131	139	147	°C
Half-Bridge Over-Temperature Hysteresis	HB <sub>(OT)(HYST)</sub>	See Note A	10	14	18	°C
LS Controller Over-Temperature Stop	LS <sub>(OT)(STOP)</sub>	See Note A	115	125	135	°C
LS Controller Over-Temperature Start	LS <sub>(OT)(START)</sub>	See Note A	66	78	90	°C

NOTES:

A. Not tested parameter. Guaranteed by design.

B. In typical LLC application circuit.

C. Normally limited by internal circuitry.

D. Not tested parameter. Based on device characterization.



#### Absolute Maximum Ratings<sup>1,2</sup> – LSR2000C

BPS Pin Voltage	
BPS Current	2 A
D1, D2 Pin Voltage	1.5 V to 150 V
FB Pin Voltage	0.3 V to 6 V
CMP Pin Voltage	
G1, G2 Pin Voltage	
IS Pin Voltage	0.3 V to 5 V
5VS Pin Voltage	
5VL Pin Voltage (wrt GP)	
FL Pin Voltage (wrt GP)	
Junction Temperature <sup>3</sup>	
Storage Temperature	
Ambient Temperature	40 °C to 105 °C
Lead Temperature <sup>4</sup>	

Notes:

Notes:

- 1. All voltages referenced to GSA, GSB unless otherwise stated  $T_{_{\rm A}}$  = 25 °C.
- Maximum ratings specified may be applied one at a time without causing permanent damage to the product. Exposure to Absolute Maximum Ratings conditions for extended periods of time may affect product reliability.
- 3. Normally limited by internal circuitry.
- 4. 1/16" from case for 5 seconds.
- 5. Absolute maximum voltage for less than 500 msec is 3 V.

#### **Thermal Resistance**

Thermal Resistance: InSOP-24D	
(θ <sub>14</sub> )	

1. Pins 2 and 12 soldered to a shared 0.36 sq. inch (232 mm²) 2 oz. (610 g/m²) copper clad.

Parameter	Conditions	Rating	Units
Ratings for UL1577			
Secondary-Side Power Rating	TAMB = 25 °C See Note A	820	mW
Secondary-Side Power Rating	TAMB = 105 °C	300	mW
Secondary-Side Current Rating	TAMB = 25 °C See Note A	34	mA
Package Characteristics			
Clearance		11.35	mm (min)
Creepage		11.35	mm (min)
Distance Through Insulation (DTI)		0.4	mm (min)
Transient Isolation Voltage		6	kV (min)
Comparative Tracking Index (CTI)		600	-

Note A: Remark regarding UL testing: the secondary side Pin 7 BPS power the IC internal controller on the secondary side and functioned as a constant current load. The pin is intended to accept a voltage in the 8-24 VDC range, which is shown on the spec, and drew 818 mW max at the high end of the voltage range.



Parameter	Symbol	<b>Conditions</b> BPS = 12 V $T_{J} = 0 \text{ °C to } 100 \text{ °C}$ (Unless Otherwise Specified)	Min	Тур	Max	Units
Secondary-Side of Safety Frequency Pin	Isolation Bar	rier				1
FMIN Frequency Range 0	F <sub>MIN(FR0)</sub>	LSR2000C H001, See Note A	21	23	24	kHz
FMIN Frequency Range 1	F <sub>MIN(FR1)</sub>	LSR2000C H002, See Note A	28	30	32	kHz
FMIN Frequency Range 2	F <sub>MIN(FR2)</sub>	LSR2000C H003, See Note A	41	45	47	kHz
FMIN Frequency Range 3	F <sub>MIN(FR3)</sub>	LSR2000C H004, See Note A	55	60	63	kHz
FMAX Frequency Range 0	F <sub>MAX(FR0)</sub>	LSR2000C H001, See Note A	123	135	141	kHz
FMAX Frequency Range 1	F <sub>MAX(FR1)</sub>	LSR2000C H002, See Note A	167	183	191	kHz
FMAX Frequency Range 2	F <sub>MAX(FR2)</sub>	LSR2000C H003, See Note A	246	270	282	kHz
FMAX Frequency Range 3	F <sub>MAX(FR3)</sub>	LSR2000C H004, See Note A	334	366	383	kHz
BPS Pin						
BPS Undervoltage Shutdown Threshold	V <sub>BPS(UV-)</sub>		7.0	7.25	7.5	V
BPS Above UV Start Threshold	V <sub>BPS(UV+)</sub>		7.3	7.55	7.8	V
BPS Start/Stop Hysteresis	V <sub>BPS(UV)(HYST)</sub>			0.29		V
BPS Pin Current in Burst	I <sub>bps(burst)</sub>	Operating in super light load switching G1, G2 floating, See Note D		600		μA
		Device with G1,G2 floating, $V_{BPS} = V_{BPS(UV+)'}$ LSR2000C-H001 (90 kHz)		9.9		mA
BPS Pin Current	T	Device with G1,G2 floating, $V_{BPS} = V_{BPS(UV+)'}$ LSR2000C-H002 (120 kHz)		12.5		mA
Consumption	I <sub>BPS(SW)</sub>	Device with G1,G2 floating, $V_{BPS} = V_{BPS(UV+)'}$ LSR2000C-H003 (180 kHz)		17.6		mA
		Device with G1,G2 floating, $V_{BPS} = V_{BPS(UV+)'}$ LSR2000C-H004 (240 kHz)		23.2		mA
5VS Pin	1		I	I	1	1
5VS Secondary Power-Up Threshold	V <sub>5VS(UV+)</sub>	$C_{SVS} = 1 \ \mu F / 10 \ V \ Ceramic$ See Note A	4.25	4.30	4.37	V
5VS Secondary Power-Down Threshold	V <sub>5VSU(V-)</sub>	$C_{svs} = 1 \ \mu F / 10 \ V \ Ceramic See \ Note \ A$	4.15	4.2	4.25	V
5VS Hysteresis	V <sub>5VS(HYST)</sub>	$C_{svs} = 1 \ \mu F / 10 \ V \ Ceramic See \ Note \ A$	0.08	0.1	0.12	V
5VS Output Voltage	V <sub>5VS</sub>	$I_{_{SVS}}$ = 0 mA, See Note A		5.18		V
IS Pin						
IS Pin Input Common Mode Voltage	V <sub>IS(CM)</sub>			2.8		V
IS Pin Input Impedance	$R_{\mathrm{IS(IN)}}$		3.2	3.7	4.3	kΩ
IS Pin Input Current Clip Threshold	I <sub>IS(CLP)</sub>		-44	-39	-32	μΑ
IS Pin Gain	G <sub>IS(CMP)</sub>		-74	-72	-70	kV/A
IS Pole	F <sub>IS(CMP)</sub>	See Note A	2.1	3.3	4.4	MHz



Parameter	Symbol	Conditions BPS = $12 V$ T <sub>J</sub> = 0 °C to 100 °C (Unless Otherwise Specified)	Min	Тур	Max	Units
Secondary-Side of Safet	y Isolation Barrie	er (cont.)			1	1
CMP Pin				1	1	1
CMP Pin Max Output Current	I <sub>CMP(OUT)(MAX)</sub>	$V_{FB} = V_{FB(STOP)(TH)}$ See Note D	50	80	140	μA
CMP Pin Burst Off 2.5 V Pull	R <sub>CMP(PULL)(2V5)</sub>	During burst-off condition See Note A		1		MΩ
FB Pin						
FB Pin REF Threshold	V <sub>FB(REF)</sub>	$V_{FB}$ when ICMP = 0	3.7	3.75	3.8	mW
FB Pin Stop Plus Threshold	V <sub>FBSTOP(TH)</sub>		3.91	3.96	4.01	V
FB Pin Stop – VFBREF	V <sub>FBSTOP(DIFF)</sub>	Difference $V_{FBSTOP(TH)} - V_{FBREF}$	194	210	226	mV
FB Pin Max Threshold	V <sub>FB(MAX)(TH)</sub>		3.72	3.77	3.81	V
FB Pin Max – VFBREF	V <sub>FB(MAX)(DIFF)</sub>	Difference V <sub>FBMAX(TH)</sub> – V <sub>FBREF</sub>	6	19	32	mV
FB Pin Min Threshold	V <sub>FB(MIN)(TH)</sub>		3.69	3.73	3.77	V
FB Pin Min – VFBREF	V <sub>FBMIN(DIFF)</sub>	Difference $V_{FBMIN(TH)} - V_{FBREF}$	-32	-19	-6	mV
FB Pin REG Threshold	V <sub>fbreg(th)</sub>		3.7	3.75	3.8	V
FB Pin REG – VFBREF	V <sub>FBREG(DIFF)</sub>	Difference $V_{FBREG(TH)} - V_{FBREF}$	-14	0	14	mV
FB Pin VREG – VMIN Difference	V <sub>FBREG(MIN)</sub>		6	19	32	mV
FB Pin VMAX – VMIN Difference	V <sub>FB(MAX)MIN</sub>		25	39	52	mV
FB Pin MINBOOST Threshold	V <sub>FBBSTN(TH)</sub>		3.54	3.60	3.65	V
FB Pin MINBOOST VFBREF	V <sub>FBBSTN(DIFF)</sub>	Difference $V_{\text{FBBSTN(TN)}} - V_{\text{FBREF}}$	-160	-148	-136	mV
FB Pin MAXBOOST Threshold	V <sub>FBBSTP(TH)</sub>		3.75	3.8	3.85	V
FB Pin MAXBOOST VFBREF	V <sub>FBBSTP(DIFF)</sub>	Difference $V_{\text{FBBSTP(TN)}} - V_{\text{FBREF}}$	42	55	68	mV
FB CMP Transconduc- tance Normal Gain	G <sub>FB(CMP)(NORM)</sub>	$T_{_{\rm J}} = 25 \ ^{\rm o}{\rm C}$ $V_{_{\rm FB}} > V_{_{\rm FBSTN(TH)}} \ \text{and} \ V_{_{\rm FB}} < V_{_{\rm FBBSTP(TH)}}$	85	95	105	μΑ/μV
FB CMP Transconduc- tance Boost Gain	G <sub>FB(CMP)(BST)</sub>	$T_{_{\rm J}} = 25 \ ^{\rm o}{\rm C} \\ V_{_{\rm FB}} < V_{_{\rm FBBSTN(TH)}} \ or \ V_{_{\rm FB}} > V_{_{\rm FBBSTP(TH)}}$	325	365	405	μΑ/μV
Transimpedance 100 °C / 25 °C Ratio	G <sub>FB(CMP)(RATIO)</sub>	See Note D		93		%
FB Pole Frequency	FB <sub>(BW)</sub>	See Note A	187	316	654	kHz
FB Pin Bleed Current	I <sub>FB(DN)</sub>	T <sub>1</sub> = 25 °C, See Note A		100		nA

Parameter	Symbol	Conditions BPS = 12 V $T_{j} = 0 \ ^{\circ}C \ to \ 100 \ ^{\circ}C$ (Unless Otherwise Specified)	Min	Тур	Max	Units
Secondary-Side of Safety	Isolation Barr	ier (cont.)			1	1
PS Pin			-1			
PS Pin Remote-OFF Threshold	$I_{_{PS(REM-)}}$		-26	-22	-17	μA
PS Pin Remote-ON Threshold	$\mathbf{I}_{PS(REM+)}$		-47	-40	-33	μA
PS Pin Remote ON-OFF Hysteresis	I <sub>ps(rem)(hyst)</sub>			18		μA
PS Pin Remote-OFF Voltage	V <sub>PS(REM-)</sub>	See Note A		0.85		V
PS Pin Remote-ON Voltage	V <sub>PS(REM+)</sub>	See Note A		0.85		V
PS Pin Selection0 Resistor	R <sub>PS(SEL0)</sub>	Required Resistor 1% E96 Series		75		kΩ
PS Pin Selection1 Resistor	R <sub>ps(sel1)</sub>	Required Resistor 1% E96 Series		75		kΩ
PS Pin Selection2 Resistor	R <sub>PS(SEL2)</sub>	Required Resistor 1% E96 Series		75		kΩ
PS Pin Selection3 Resistor	R <sub>ps(sel3)</sub>	Required Resistor 1% E96 Series		169		kΩ
PS Pin Selection4 Resistor	R <sub>PS(SEL4)</sub>	Required Resistor 1% E96 Series		169		kΩ
PS Pin Selection5 Resistor	R <sub>ps(sel5)</sub>	Required Resistor 1% E96 Series		255		kΩ
PS Pin Selection6 Resistor	R <sub>PS(SEL6)</sub>	Required Resistor 1% E96 Series		340		kΩ
PS Pin Selection7 Resistor	R <sub>PS(SEL7)</sub>	Required Resistor 1% E96 Series		499		kΩ
1 and G2 Pins						
G1, G2 Clamp Voltage (Freq 0,1)	V <sub>G1(CLMP)</sub> V <sub>G2(CLMP)</sub>	BPS = 15 V, LSR2000C H001,H002	10.3	11.7	13.5	v
G1, G2 Clamp Voltage (Freq 2,3)	V <sub>G1(CLMP)</sub> V <sub>G2(CLMP)</sub>	BPS = 15 V, LSR2000C H003,H004	5.0	6.0	7.0	V
G1, G2 BP Voltage Drop	V <sub>G1(CLMP)(DROP)</sub> V <sub>G2(CLMP)(DROP)</sub>	BPS = 15 V See Note A	0.65	1.1	1.5	V
G1, G2 Source Current	$I_{G1(SOURCE)} \\ I_{G2(SOURCE)}$	BPS = 15 V, VG1 = VG2 = 0 V	0.65	1.1	1.5	A
G1, G2 Sink Current	I <sub>G1(SINK)</sub> I <sub>G2(SINK)</sub>	BPS = 15 V, VG1 = VG2 = VG1(CLMP)	1.6	2	2.2	A



		1				
Parameter	Symbol	<b>Conditions</b> BPS = 12 V $T_j = 0 \text{ °C to } 100 \text{ °C}$ (Unless Otherwise Specified)	Min	Тур	Max	Units
Secondary-Side of Safety	Isolation Ba	rrier (cont.)				
D1 and D2 Pin				1	1	1
D1, D2 Breakdown Voltage	$BV_{d1D2}$		150			v
D1, D2 External Resistor	R <sub>D1D2(EXT)</sub>	Recommended external R between SR FET Drain and D1, D2 pin	200		1500	Ω
D1, D2 Inverse Current	$I_{\text{D1D2(INV)}}$	Allowed current out of D1, D2 when below GND	-5			mA
D1, D2 SR On Threshold	V <sub>D1D2ON(TH)</sub>	See Note E	-275	-250	-210	mV
D1, D2 SR Off Threshold	$V_{\text{D1D2OFF(TH)}}$	See Note E	3	8.5	12.5	mV
D1, D2 SR Off Threshold Matching	$\Delta V_{\text{D1D2OFF}}$		-2.6	0	2.6	mV
D1, D2 Ouput Bias Current – Off	$\mathrm{I}_{_{\text{D1D2OFF}}}$	Bias Current Out of D1, D2 at $V_{\text{D1D2OFF(TH)}}$	-17	-13	-9	μΑ
Secondary Control Ove	r-Temperat	ure				
Secondary Control Over-Temperature Stop	SC <sub>(OT)(STOP)</sub>	See Note A	123	130	137	°C
Secondary Control Over-Temperature Start	SC <sub>(OT)(START)</sub>	See Note A		75		°C
Primary-Side of Safety Is	olation Barrie	er .			'	, 
5VL Pin		,		1	1	1
5VL Power-Up Threshold	V <sub>5VL(UV+)</sub>	C5VL = 1 $\mu$ F / 10 V Ceramic	3	3.5	4	v
5VL Power-Up Hysteresis	V <sub>5VL(HYST)</sub>	C5VL = 1 $\mu$ F / 10 V Ceramic		1.5		V
FL Pin		·		·		·
FL - Logic 1 Output Voltage	$V_{FL(1)}$	$I_{_{FL}}$ = 10 mA, 5VL = 5 V	4.55	4.7	4.929	V
FL - Logic 0 Output Voltage	V <sub>FL(0)</sub>	$I_{FL} = +10 \text{ mA}$	0.17	0.25	0.42	V

NOTES:

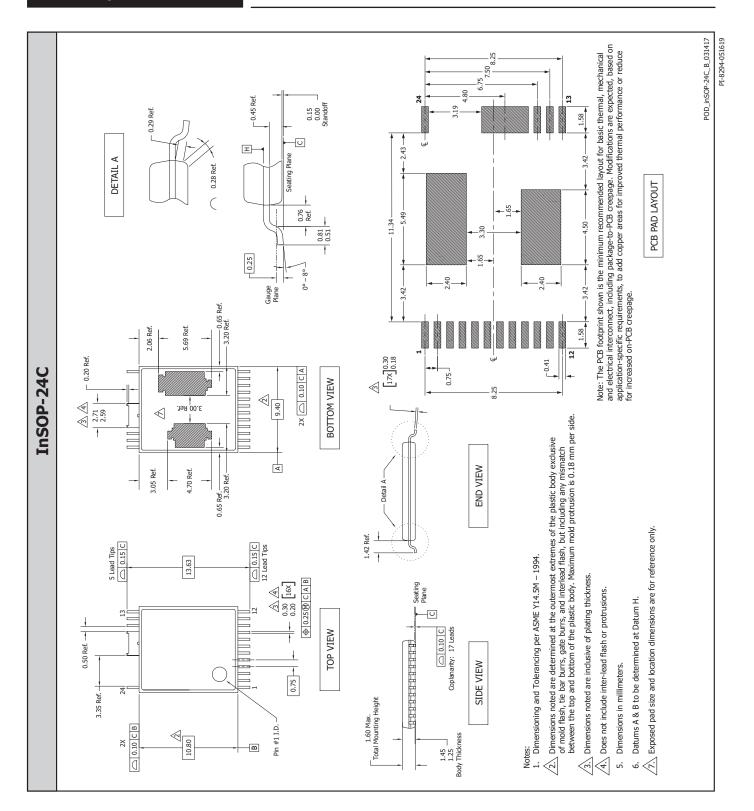
A. Not tested parameter. Guaranteed by design.B. In typical LLC application circuit.

C. Normally limited by internal circuitry.

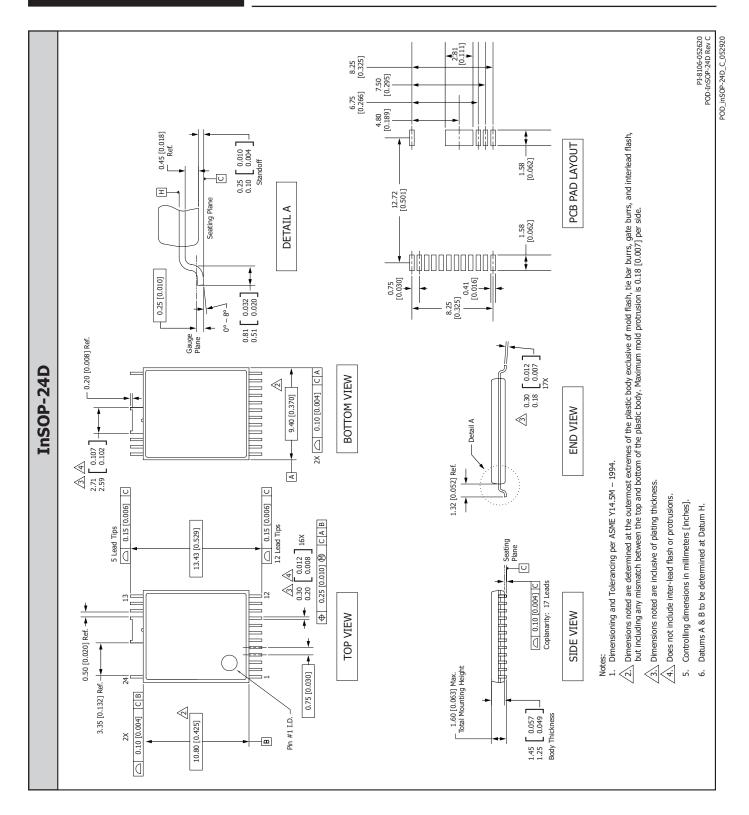
D. Not tested parameter. Based on device characterization.

E. Production test limits. Observed operational threshold for SR MOSFET drain (D1, D2), also depends on chosen D1, D2 resistors  $\rm R_{\rm D1D2(EXT)}$  values.





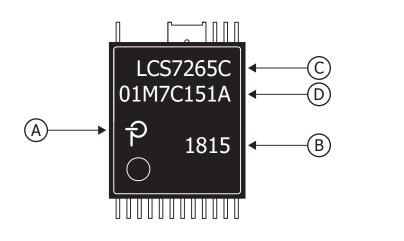






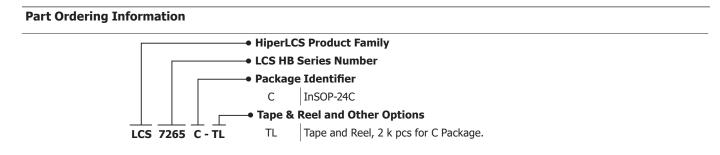
## PACKAGE MARKING





- A. Power Integrations Registered Trademark
- B. Assembly Date Code (last two digits of year followed by 2-digit work week)
- C. Product Identification (Part #/Package Type)
- D. Lot Identification Code

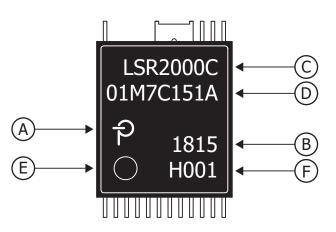
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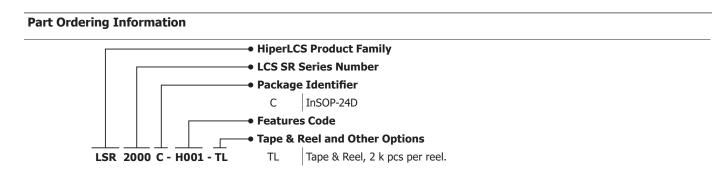
## **PACKAGE MARKING**

## InSOP-24D



- A. Power Integrations Registered Trademark
- B. Assembly Date Code (last two digits of year followed by 2-digit work week)
- C. Product Identification (Part #/Package Type)
- D. Lot Identification Code
- E. Pin 1 Indicator
- F. Features Code

PI-9311-021621





Feature Code	Frequency Range	Nominal Frequency
H001	0	90 kHz
H002	1	120 kHz
H003	2	180 kHz
H004	3	240 kHz

## MSL Table

Part Number	MSL Rating
LCS7260C	3
LCS7262C	3
LCS7265C	3
LSR2000C	3



Revision	Notes	Date
В	Code A release.	03/21
С	Updates.	03/22

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